

Analysis of barrier inhomogeneities of P-type Al/4H-SiC Schottky barrier diodes

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Analysis of deep level centers in GaAs pin-diode structures

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Analysis of deep level spectrum in GaAs p+-p-i-n-n+ structures

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Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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